

Quarterly Reliability Monitoring Results

Quarters: Q1/2022 to Q4/2023

Based on structural similarity

Supplier Nexperia B.V.		User Part Number						
		PMBTA06-Q						
Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		Part Description						
		Nexperia DHAM Small Signal Bipolar Transistor						
		SMD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	1674	70490	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
		Tj = Tjmax, Vr = 100% of max. datasheet						
# B1	Bias	reverse voltage	1000 hours	415	18680	0		
	TC	JESD22-A104				_		
# A4	Temperature Cycling	-65 °C to Tjmax, not to exceed 150°C	1000 cycles	343	15360	0		
	UHAST	JESD22-A118						
# A3 or	Undsi Unbiased HAST	Tamb = 130 °C, RH = 85 %	— 96 hours	362	15920	0		
	Olibiased FIAST							
	AC	JESD22-A102 Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)						
AS all	Autociave	11e33dre = 203 ki d (23.7 p3id)						
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	Temperature Reverse Bias		1000 hours	343	15360	0		
AZ dIL	remperature Reverse Blus	MIL-STD-750 Method 1037	1000 110015	343	13300	U		
	IOL	ton = toff, devices powered to insure ΔT_i =						
# A5	Intermittent Operating Life		1000 hours	343	15360	0		
- 77	End operating Life	2.2. 2.3. 2000 0,000	1000 110015	242	13300	U		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat		10 s	283	8490	0		
₇ C0	SD		10.5	203	0430	U		
# C10	Solderability	J-STD-002		214	6420	0		
11 Tho ma	22.30.00			414	0420	U		

^[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	18680	0	0,23	4,40E+09

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